

SANYO

No.2124A

DS462

Silicon Epitaxial Planar Type

High-Voltage Switching Diode

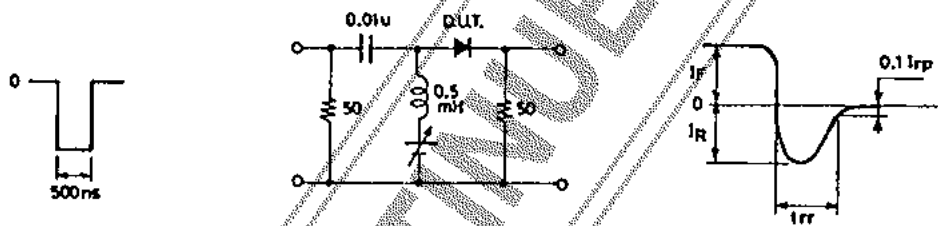
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Condition	Value	Unit
Peak Reverse Voltage	V_{RM}		-250	V
Reverse Voltage	V_R		-200	V
Peak Forward Current	I_{FM}		600	mA
Average Rectified Current	I_O		200	mA
Surge Forward Current	I_{FSM}	10msec pulse	2000	mA
Allowable Power Dissipation	P		400	mW
Junction Temperature	T_j		175	°C
Storage Temperature	T_{stg}		-65 to +175	°C

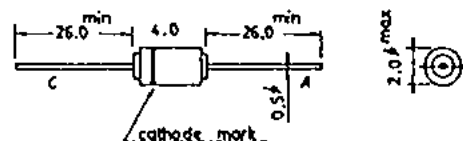
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Condition	min	typ	max	Unit
Forward Voltage	V_{F1}	$I_F = 1\text{mA}$			0.8	V
	V_{F2}	$I_F = 100\text{mA}$	0.95	1.2		V
Reverse Current	I_R	$V_R = -200\text{V}$		-0.5		μA
Interterminal Capacitance	c	$V_R = 0\text{V}, f = 1\text{MHz}$	1.0			pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10\text{mA}, R_L = 50\Omega$			60	ns

Reverse Recovery Time Test Circuit



Case Outline 1080 (unit: mm)

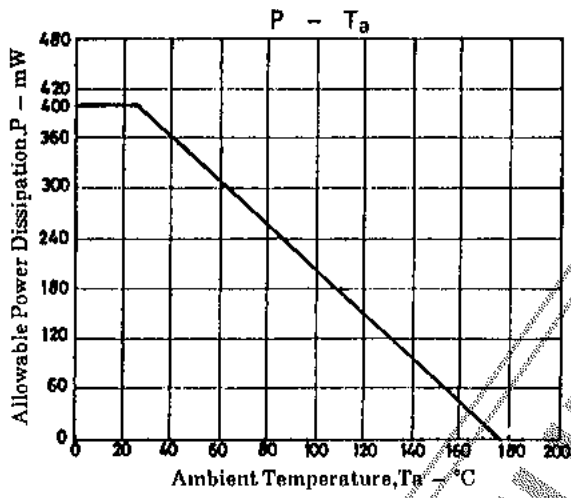
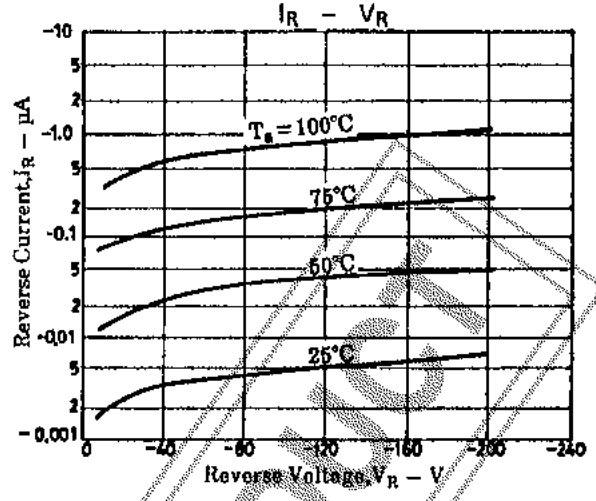
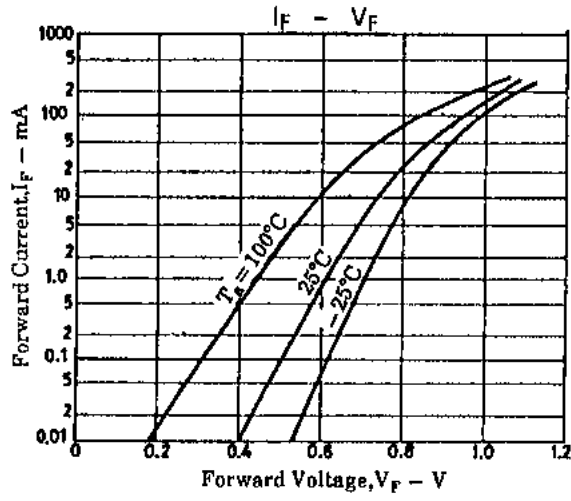


C: Cathode
A: Anode

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Specifications and information herein are subject to change without notice.

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DISCONTINUED PRODUCT